# ATENT COOPERATION TREALY

From the INTERNATIONAL SEARCHING AUTHORITY

To: SEMICONDUCTOR ENERGY LABORATORY CO., LTD.

398, Hase, Atsugi -shi, Kanagawa 2430036 Japan

# **PCT**

WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY (PCT Rule 43 bis.1)

Date of mailing 27.12.2005 (day/month/year) Applicant's or agent's file reference FOR FURTHER ACTION 00000PCT8160 See paragraph 2 below International application No. International filing date (day/month/year) Priority date (day/month/year) PCT/JP2005/017223 13.09.2005 15.09.2004 International Patent Classification (IPC) or both national classification and IPC Int.Cl. H01L29/786 (2006.01), H01L21/336 (2006.01), G02F1/1368 (2006.01) Applicant SEMICONDUCTOR ENERGY LABORATORY CO., LTD.

1.	This	This opinion contains indications relating to the following items:					
	Y	Box No. I	Basis of the opinion				
Box No. II Priority			Priority				
		Box No. III	Non-establishment of opinion with regard to novelty, inventive step and industrial applicability				
Box No. IV Lack of unity of invention			Lack of unity of invention				
			Reasoned statement under Rule 43 bis.1(a)(i) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement				
		Box No. VI	Certain documents cited				
		Box No. VII	Certain defects in the international application				
		Box No. VIII	Certain observations on the international application				
2.	FUR7	THER ACTION					
•	If a demand for international preliminary examination is made, this opinion will be considered to be a written opinion of the International Preliminary Examining Authority ("IPEA") except that this does not apply where the applicant chooses an Authority other than this one to be the IPEA and the chosen IPEA has notified the International Bureau under Rule 66.1bis(b) that written opinions of this International Searching Authority will not be so considered.						
	If this opinion is, as provided above, considered to be a written opinion of the IPEA, the applicant is invited to submit to the IPEA a written reply together, where appropriate, with amendments, before the expiration of 3 months from the date of mailing of Form PCT/ISA/220 or before the expiration of 22 months from the priority date, whichever expires later.						
	For further options, see Form PCT/ISA/220.						
3	For further details, see notes to Form PCT/ISA/220						

Date of completion of this opinion 25.11	.2005	
Name and mailing address of the ISA/JP	Authorized officer	4M 9449
Japan Patent Office	Shigemasa MATSUDA	<u> </u>
3-4-3, Kasumigaseki, Chiyoda-ku, Tokyo 100-8915, Ja		3462

Form PCT/ISA/237 (cover sheet) (April 2005)

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# WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY

International application No.

PCT/JP2005/017223

Вс	x No. I	Basis of the opinion						
	With	aggred to the learners this activity has been earliest at 1 1 1 C						
1.		th regard to the language, this opinion has been established on the basis of: the international application in the language in which it was filed						
	11	a translation of the international application into , which is the language of a translation furnished for the purposes of international search (Rules 12.3(a) and 23.1(b)).						
		removement farmones for the purposes of merhadonal scales (Rules 12.5(a) and 25.1(b)).						
2.	<ol> <li>With regard to any nucleotide and/or amino acid sequence disclosed in the international application and necessary claimed invention, this opinion has been established on the basis of:</li> </ol>							
	a. type	of material						
		a sequence listing						
		table(s) related to the sequence listing						
		( )						
	b. form	nat of material						
		on paper						
		in electronic form						
		of filing/furnishing						
		contained in the international application as filed						
		filed together with the international application in electronic form						
		furnished subsequently to this Authority for the purposes of search						
3.		n addition, in the case that more than one version or copy of a sequence listing and/or table(s) relating thereto has been iled or furnished, the required statements that the information in the subsequent or additional copies is identical to that n the application as filed or does not go beyond the application as filed, as appropriate, were furnished.						
4.	Additio	nal comments:						
		and commons.						
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# WRITTEN OPINION OF THE INTERNATIONAL SEARCHING AUTHORITY

International application No.

PCT/JP2005/017223

citations and explanations supporting such statement						
1.	Statement			·		
	Novelty (N)	Claims	1-14	YES		
		Claims		NO		
	Inventive step (IS)	Claims	·	YES		
		Claims	1-14	NO		
	Industrial applicability (IA)	Claims	1-14	YES		
		Claims		·		

## 2. Citations and explanations:

D1:JP 2001-281694 A (SEMICONDUCTOR ENERGY LABORATORY CO., Ltd.) 2001.10.10, Figs.4,6,17,18 (Family: None)

D2:JP 6-202146 A(FUJITSU, Ltd.)1994.07.22, Whole Document (Family: None)

D3:JP 2001-281704 A (SEMICONDUCTOR ENERGY LABORATORY CO., Ltd.)

2001.10.10, Fig.16 & US 2002/0110941 A1

D4:JP 7-312425 A (HITACHI, Ltd.) 1995.11.28, Fig.3(Family: None)

### Claims1, 2, 5-14

In the cited document D1,

A semiconductor device, which is a mobile information terminal etc., comprising TFTs having an electrode by stacking a first conductive layer (Ti) in contact with the semiconductor thin film and a second conductive layer (Al) on the first conductive layer. And, the first conductive layer has a portion projected from an end portion of the second conductive layer, wherein ITO, which is for the light-emitting element or the liquid crystal element, is in contact with the portion of the first conductive film. In the cited document D2,

An electrode, such an art, has a tapered portion in order to securely connect.

Therefore, it is perceived that a person skilled in the art could have easily made the invention by applying the technique of cited document D2 to the semiconductor device of cited document D1.

### Claim3,4

In the cited document D3,

A multilayer electrode, wherein a side surface portion of a first conductive layer has a smaller tapered angle than that of a second conductive layer. In the cited document D4,

A multilayer electrode, wherein a side surface portion of a first conductive layer has a larger tapered angle than that of a second conductive layer. Therefore, it is perceived that a person skilled in the art could have easily made the invention by applying the techniques of cited documents D2-4 to the semiconductor device of cited document D1.